ABSTRACT OF THE DISCLOSURE

The semiconductor light-emitting device of the present invention includes a first semiconductor layer of a first conductivity type formed substantially in a uniform thickness on a substrate and a second semiconductor layer of a second conductivity type formed substantially in a uniform thickness on the first semiconductor layer. The device further includes an active layer, formed substantially in a uniform thickness between the first semiconductor layer and the second semiconductor layer, for generating emission light. The device also comprises a first electrode for supplying a drive current to the first semiconductor layer and a second electrode for supplying a drive current to the second semiconductor layer. The device is adapted that the first or second electrode is a divided electrode comprising a plurality of conductive members spaced apart from each other.